

**Description**

The SX100P02D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -20V$   $I_D = -100A$

$R_{DS(ON)} < 6.5m\Omega$  @  $V_{GS}=4.5V$

**Application**

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-100	A
$I_D@T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-40	A
$IDM$	Pulsed Drain Current <sup>2</sup>	-300	A
$P_D@T_c=25^\circ C$	Total Power Dissipation <sup>3</sup>	30	W
$P_D@T_c=70^\circ C$	Total Power Dissipation <sup>3</sup>	19	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{eJA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62.5	°C/W
$R_{eJC}$	Thermal Resistance Junction-Case <sup>1</sup>	1.1	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=-250\mu\text{A}$	-20	-22	---	V
$\Delta BVDSS/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.012	---	$\text{V}/^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5\text{V}$ , $I_D=-15\text{A}$	---	4.5	6.5	$\text{m}\Omega$
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-2.5\text{V}$ , $I_D=-10\text{A}$	---	6.0	8.0	$\text{m}\Omega$
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu\text{A}$	-0.45	-0.65	-1.2	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	2.94	---	$\text{mV}/^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-20\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 12\text{V}$ , $V_{DS}=0\text{V}$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-10\text{A}$	---	43	---	S
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-15\text{V}$ , $V_{GS}=-4.5\text{V}$ , $I_D=-10\text{A}$	---	63	---	nC
Qgs	Gate-Source Charge		---	9.1	---	
Qgd	Gate-Drain Charge		---	13	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-10\text{V}$ , $V_{GS}=-4.5\text{V}$ , $R_G=3.3\Omega$ , $I_D=-10\text{A}$	---	15.8	---	ns
$T_r$	Rise Time		---	76.8	---	
Td(off)	Turn-Off Delay Time		---	193	---	
$T_f$	Fall Time		---	186.4	---	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$	---	5783	---	pF
Coss	Output Capacitance		---	509	---	
Crss	Reverse Transfer Capacitance		---	431	---	
IS	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0\text{V}$ , Force Current	---	---	-10.7	A
ISM	Pulsed Source Current <sup>2,4</sup>		---	---	-60	A
VSD	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0\text{V}$ , $I_S=-1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	-1.2	V
trr	Reverse Recovery Time	$ I_F =-10\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	27	---	nS
Qrr	Reverse Recovery Charge		---	17.8	---	nC

**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3、The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4、The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

## Typical Characteristics

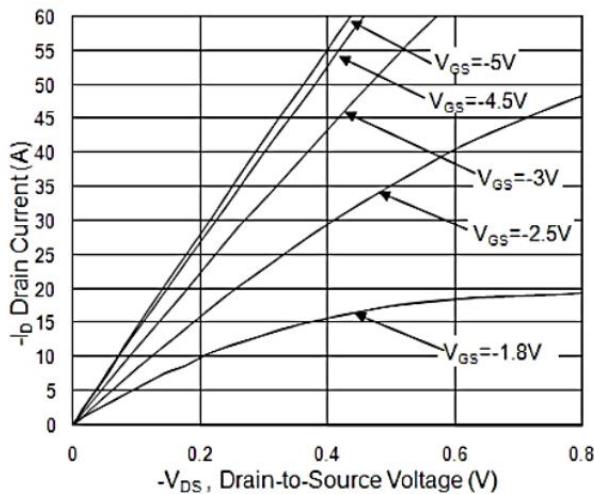


Fig.1 Typical Output Characteristics

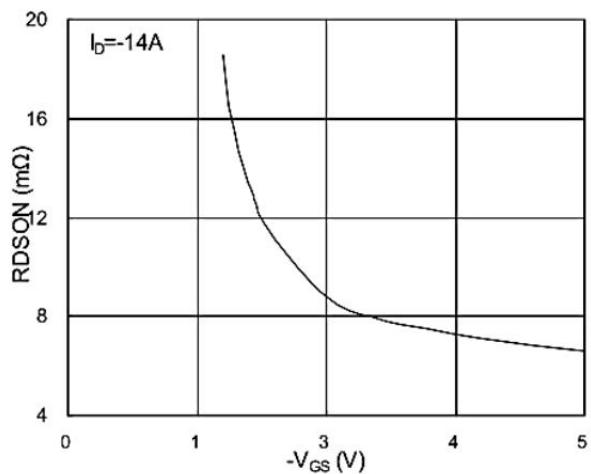


Fig.2 On-Resistance vs. G-S Voltage

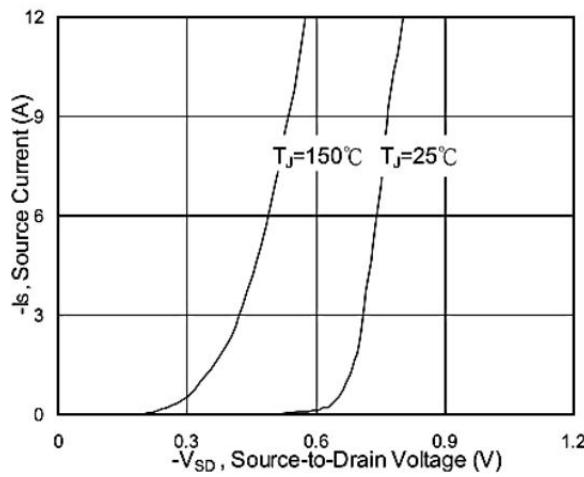


Fig.3 Forward Characteristics of Reverse

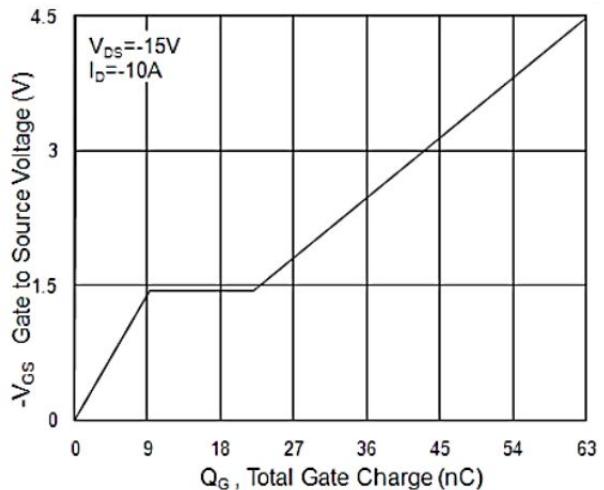


Fig.4 Gate-charge Characteristics

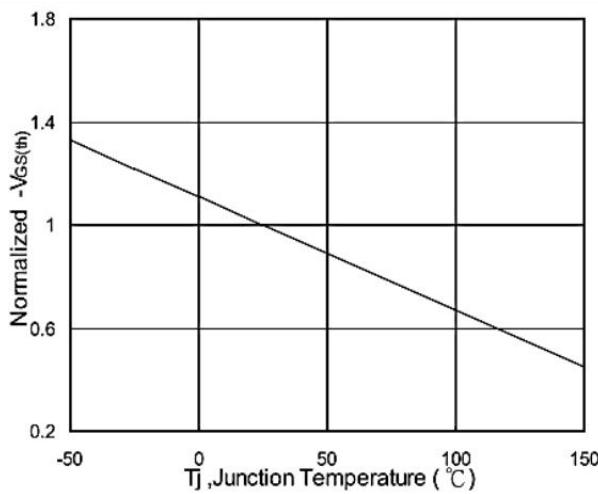


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

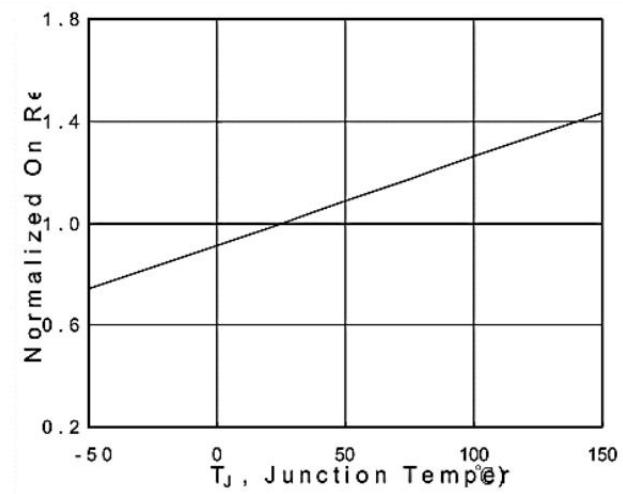
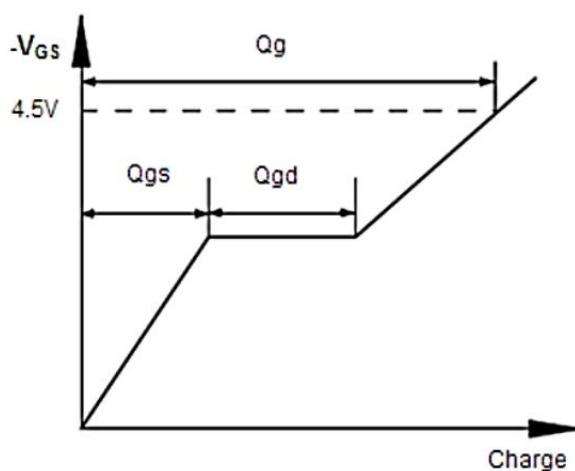
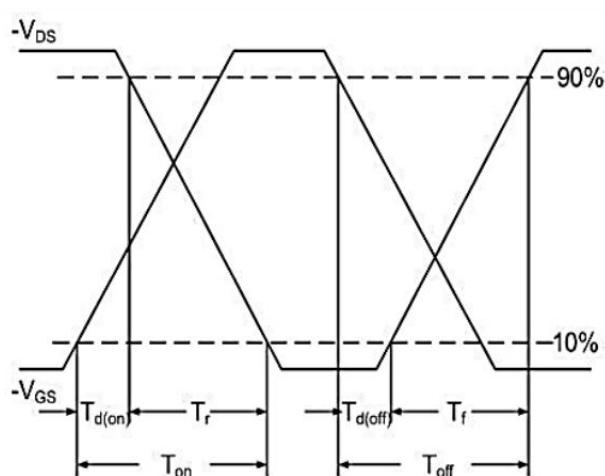
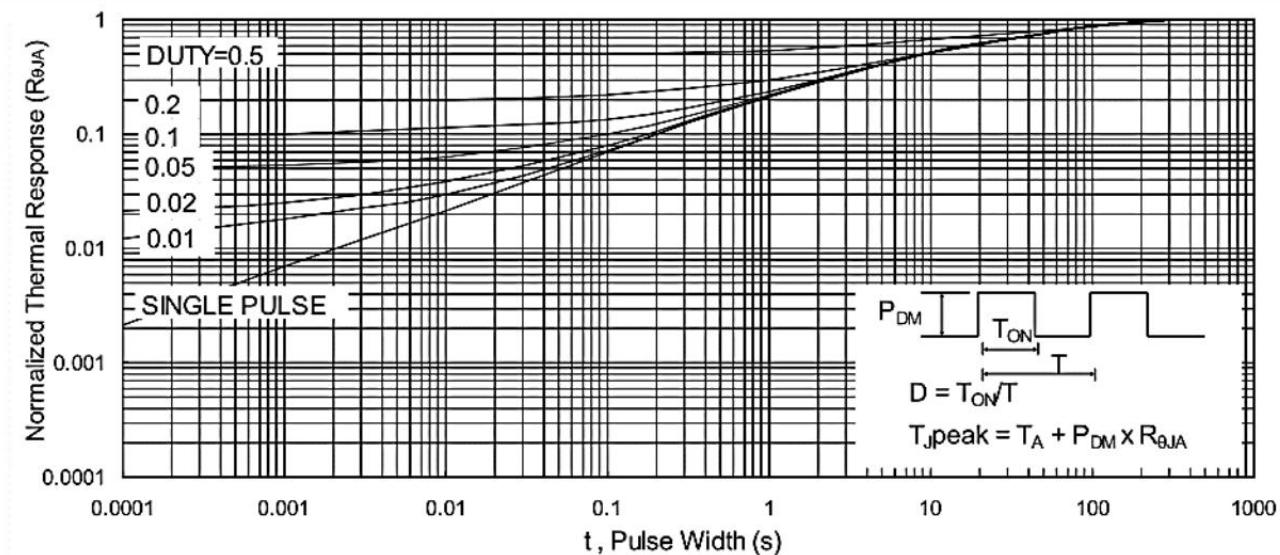
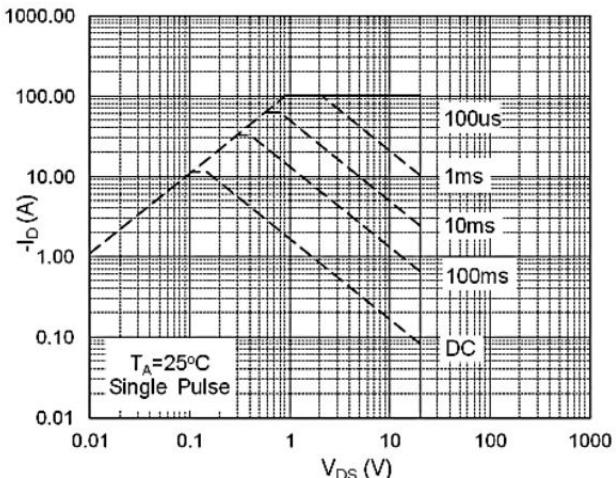
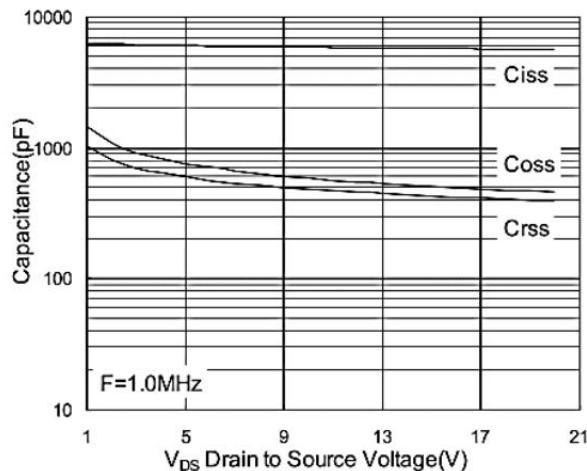
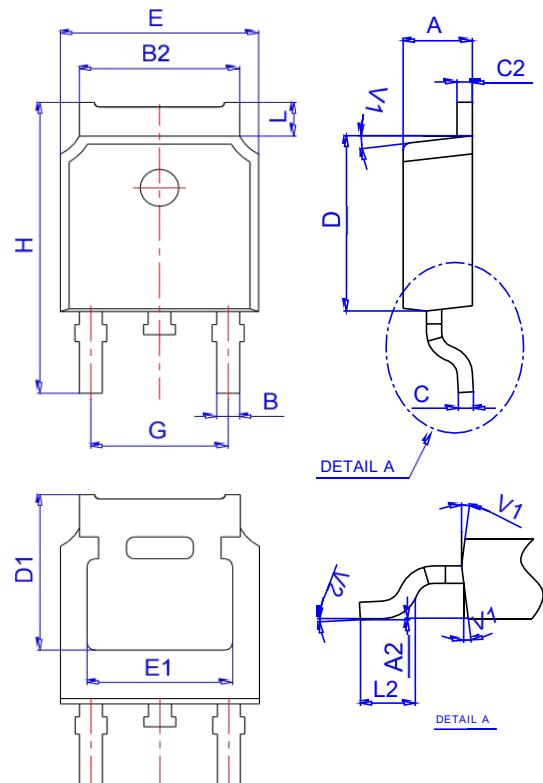


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

### Typical Characteristics



## Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500